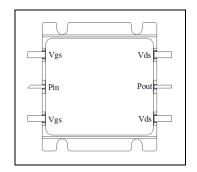
### 2.0-6.0GHz, 80W, GaN Fully matched PA Module

### **Description**

The XMAH2060-80H3 is a 80-watt Psat capable, single stage integrated IMFET, designed for broad band applications, with frequencies from 2.0 to 6.0GHz. The module is 50  $\Omega$  input/output matched and requires minimal external components.

The module implements multiple GaN active dice and its matching network within highly compact 30.8\*27.4mm metal RF package with excellent capability for heat dissipation.



### Pout at Vds=28V, Idq=300mA

Freq(MHz)	Pin(dBm)	Pout(dBm)	Pout(W)	IDS(A)	Gain(dB)	Eff(%)	2nd	3rd
							Harmonic	Harmonic
2000	43.30	50.86	121.9	6.80	7.56	64.0	-20.4	-13.9
2500	42.95	50.41	109.9	6.73	7.46	58.3	-17.9	-28.3
3000	42.50	49.90	97.7	8.56	7.40	40.8	-17.5	-46.0
3400	42.20	49.20	83.2	9.40	7.00	31.6	-23.7	-47.0
3500	44.00	51.07	127.9	11.82	7.07	38.7	-26.1	-48.1
4000	43.70	50.80	120.2	9.23	7.10	46.5	-40.3	-40.4
4200	42.20	49.20	83.2	8.26	7.00	36.0		
4500	43.30	50.40	109.6	10.31	7.10	38.0		
5000	42.92	50.26	106.2	9.68	7.34	39.2		
5500	42.55	50.70	117.5	10.77	8.15	39.0		
6000	38.65	49.11	81.5	7.26	10.46	40.1		

### **Applications**

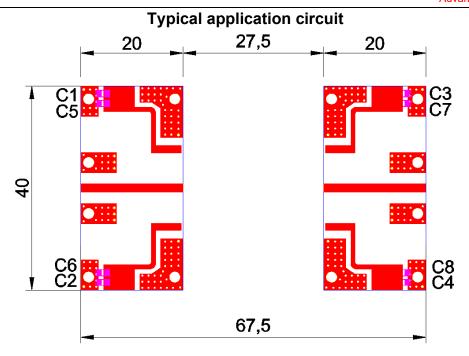
- Ultra Broadband Amplifiers within S/C band
- Test Instrumentation
- EMC Amplifier Drivers
- 2-way Radios

#### **Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
DrainSource Voltage	$V_{\scriptscriptstyle DSS}$	150	Vdc
GateSource Voltage	$V_{\sf GS}$	-10 to +2	Vdc
Operating Voltage	$V_{DD}$	+32	Vdc
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	T <sub>c</sub>	+150	°C
Operating Junction Temperature	T,	+225	°C

#### **Table 2. Thermal Characteristics**

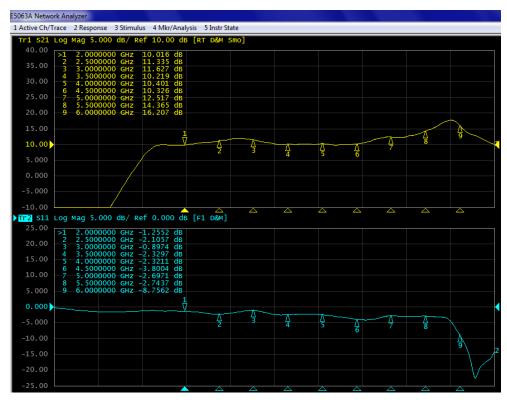
Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	Dava	0.0	00/11/
T <sub>C</sub> = 25°C, Pout=80W, FEA	Rejc	0.8	°C/W



Component	Description	Suggestion
C1 C2 C3 C4	10 uF	1210
C5 C6 C7 C8	100 pF	MQ301111
PCB	30Mil Rogers 4350	

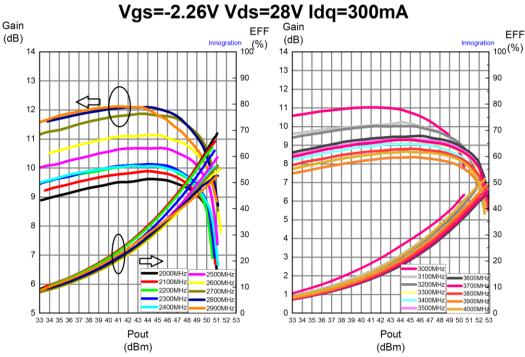
### **TYPICAL CHARACTERISTICS**

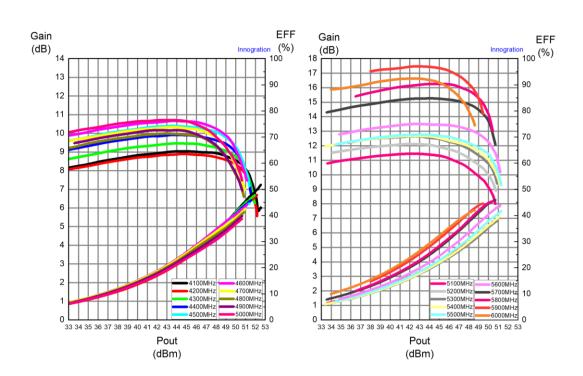
Figure 1. Network analyzer output S11/S21 (Pin=0dBm, Idq=500mA)





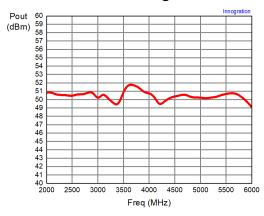
# XMAH2060-80H3\_rev6 Pulse 100us 10%

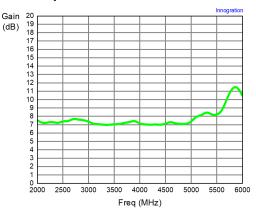


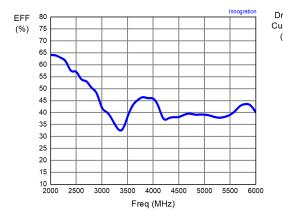


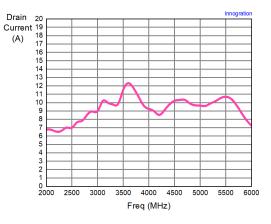


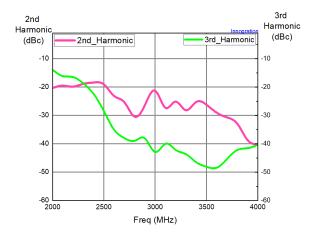
### XMAH2060-80H3\_Rev6 CW Test Vgs=-2.28V Vds=28V Idq=220mA



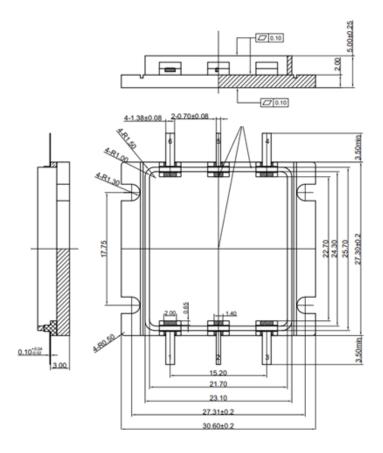








#### **Package Dimensions** (Unit:mm)



#### **Revision history**

Table 6. Document revision history

Date	Revision	Datasheet Status
2025/8/19	Rev 1.0	Advanced Datasheet
2025/9/14	Rev 2.0	Modify the Rth

#### Application data based on JF-25-18

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